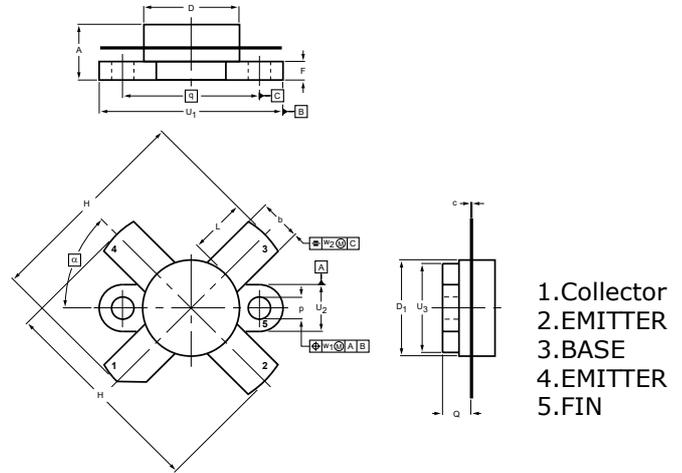


DESCRIPTION

designed primarily for SSB communications. This device utilizes state-of-the-art diffused emitter ballasting for improved ruggedness and reliability.

FEATURES

- Output Power: 125W(Min)
- Power Gain: 15 dB Min@30M, 28V
- Intermodulation Distortion: -30dB Max@30M, 28V



DIMENSIONS

NOTE: ALL ELECTRODES ARE ISOLATED FROM FLANGE.

UNIT	A	b	c	D	D ₁	F	H	L	p	Q	q	U ₁	U ₂	U ₃	w ₁	w ₂	α
mm	7.27 6.17	5.82 5.56	0.16 0.10	12.86 12.59	12.83 12.57	2.67 2.41	28.45 25.52	7.93 6.32	3.30 3.05	4.45 3.91	18.42	24.90 24.63	6.48 6.22	12.32 12.06	0.51	1.02	45°
inches	0.286 0.243	0.229 0.219	0.006 0.004	0.506 0.496	0.505 0.495	0.105 0.095	1.120 1.005	0.312 0.249	0.130 0.120	0.175 0.154	0.725	0.98 0.97	0.255 0.245	0.485 0.475	0.02	0.04	

MAXIMUM RATINGS

CHARACTERISTICS	SYMBOL	RATINGS	UNITS
Collector-Base Voltage	V _{CB0}	70	V
Collector-Emitter Voltage	V _{CES}	70	V
Collector-Emitter Voltage	V _{CEO}	40	V
Collector Current	I _c	20	A
Emitter-Base Voltage	V _{EBO}	4	V
Collector Power Dissipation	P _{DISS}	270	W
Storage Temperature Range	T _{STG}	-65 to 150	°C

ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX	UNITS
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _c =200mA, I _B =0	40	-	-	V
Collector-Emitter Breakdown Voltage	V _{(BR)CES}	I _c =100mA, V _{EB} =0	70	-	-	V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E =1mA, I _c =0	4	-	-	V
Collector Cutoff Current	I _{CB0}	V _{CB} =80V, I _E =0	-	-	1	mA
DC Current Gain	h _{FE}	V _{CE} =5V, I _c =10A	10	-	-	
Collector Output Capacitance	C _{ob}	V _{CB} =28V, I _E =0 f=1MHz	-	280	-	pF
Power Gain	G _P	V _{CC} =28V, P _{OUT} =125	15.0	16.0	-	dB
Input Power	P _i	W, I _{cQ} =100mA,	-	3.95	-	W
Intermodulation Distortion	IMD	f=30M, 30.001MHz	-	-	-30	dB

Note : Above parameters , ratings , limits and conditions are subject to change.